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(54) Title: METHOD AND APPARATUS FOR DRYING A SEMICONDUCTOR WAFER

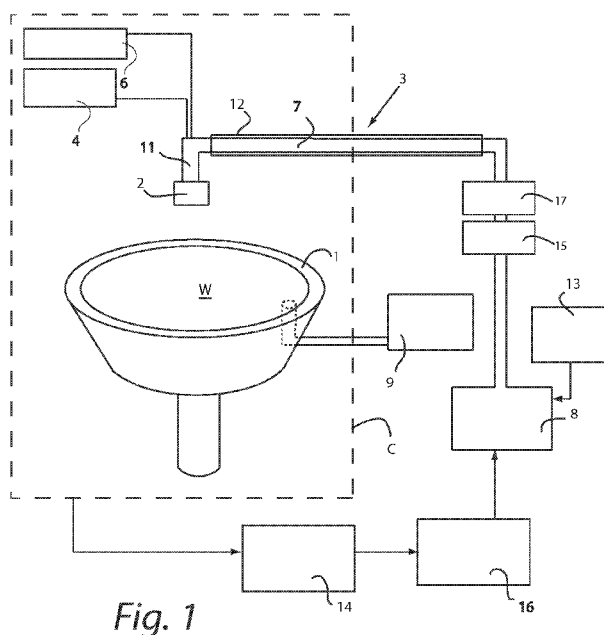


Fig. 1

(57) Abstract: 4303-1043 22 ABSTRACT OF THE DISCLOSURE A method and apparatus for drying semiconductor wafers uses hot isopropyl alcohol in liquid form at temperatures above 60°C and below 82°C. The use of hot IPA better avoids pattern collapse and permits reduced consumption of IPA. The wafer temperature can be maintained by applying hot deionized water to the opposite wafer side and by evaporating the hot IPA from the wafer surface using heated nitrogen gas.

**Declarations under Rule 4.17:**

- *as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))*
- *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))*

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